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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I <sup>2</sup> C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	93
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 16x12b SAR; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	120-VFBGA
Supplier Device Package	120-BGA (7x7)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/silicon-labs/efm32gg11b420f2048gl120-br">https://www.e-xfl.com/product-detail/silicon-labs/efm32gg11b420f2048gl120-br</a>

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### 3.10.2 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the microcontroller. The flash memory is readable and writable from both the Cortex-M and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block, whereas the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in energy modes EM0 Active and EM1 Sleep.

### 3.10.3 Linked Direct Memory Access Controller (LDMA)

The Linked Direct Memory Access (LDMA) controller allows the system to perform memory operations independently of software. This reduces both energy consumption and software workload. The LDMA allows operations to be linked together and staged, enabling sophisticated operations to be implemented.

### 3.10.4 Bootloader

All devices come pre-programmed with a UART bootloader. This bootloader resides in flash and can be erased if it is not needed. More information about the bootloader protocol and usage can be found in *AN0003: UART Bootloader*. Application notes can be found on the Silicon Labs website ([www.silabs.com/32bit-appnotes](http://www.silabs.com/32bit-appnotes)) or within Simplicity Studio in the **[Documentation]** area.

#### 4.1.4 DC-DC Converter

Test conditions: L\_DCDC=4.7  $\mu$ H (Murata LQH3NPN4R7MM0L), C\_DCDC=4.7  $\mu$ F (Samsung CL10B475KQ8NQNC), V\_DCDC\_I=3.3 V, V\_DCDC\_O=1.8 V, I\_DCDC\_LOAD=50 mA, Heavy Drive configuration, F\_DCDC\_LN=7 MHz, unless otherwise indicated.

**Table 4.4. DC-DC Converter**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input voltage range	V <sub>DCDC_I</sub>	Bypass mode, I <sub>DCDC_LOAD</sub> = 50 mA	1.8	—	V <sub>VREGVDD_MAX</sub>	V
		Low noise (LN) mode, 1.8 V output, I <sub>DCDC_LOAD</sub> = 100 mA, or Low power (LP) mode, 1.8 V output, I <sub>DCDC_LOAD</sub> = 10 mA	2.4	—	V <sub>VREGVDD_MAX</sub>	V
		Low noise (LN) mode, 1.8 V output, I <sub>DCDC_LOAD</sub> = 200 mA	2.6	—	V <sub>VREGVDD_MAX</sub>	V
Output voltage programmable range <sup>1</sup>	V <sub>DCDC_O</sub>		1.8	—	V <sub>VREGVDD</sub>	V
Regulation DC accuracy	ACC <sub>DC</sub>	Low Noise (LN) mode, 1.8 V target output	TBD	—	TBD	V
Regulation window <sup>4</sup>	WIN <sub>REG</sub>	Low Power (LP) mode, LPCMPBIASEMxx <sup>3</sup> = 0, 1.8 V target output, I <sub>DCDC_LOAD</sub> ≤ 75 $\mu$ A	TBD	—	TBD	V
		Low Power (LP) mode, LPCMPBIASEMxx <sup>3</sup> = 3, 1.8 V target output, I <sub>DCDC_LOAD</sub> ≤ 10 mA	TBD	—	TBD	V
Steady-state output ripple	V <sub>R</sub>		—	3	—	mVpp
Output voltage under/overshoot	V <sub>OV</sub>	CCM Mode (LNFORCECCM <sup>3</sup> = 1), Load changes between 0 mA and 100 mA	—	25	TBD	mV
		DCM Mode (LNFORCECCM <sup>3</sup> = 0), Load changes between 0 mA and 10 mA	—	45	TBD	mV
		Overshoot during LP to LN CCM/DCM mode transitions compared to DC level in LN mode	—	200	—	mV
		Undershoot during BYP/LP to LN CCM (LNFORCECCM <sup>3</sup> = 1) mode transitions compared to DC level in LN mode	—	40	—	mV
		Undershoot during BYP/LP to LN DCM (LNFORCECCM <sup>3</sup> = 0) mode transitions compared to DC level in LN mode	—	100	—	mV
DC line regulation	V <sub>REG</sub>	Input changes between V <sub>VREGVDD_MAX</sub> and 2.4 V	—	0.1	—	%
DC load regulation	I <sub>REG</sub>	Load changes between 0 mA and 100 mA in CCM mode	—	0.1	—	%

## 4.1.7 Current Consumption

### 4.1.7.1 Current Consumption 3.3 V without DC-DC Converter

Unless otherwise indicated, typical conditions are: VREGVDD = AVDD = DVDD = 3.3 V. T = 25 °C. DCDC is off. Minimum and maximum values in this table represent the worst conditions across supply voltage and process variation at T = 25 °C.

**Table 4.7. Current Consumption 3.3 V without DC-DC Converter**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM0 mode with all peripherals disabled	I <sub>ACTIVE</sub>	72 MHz HFRCO, CPU running Prime from flash	—	120	—	μA/MHz
		72 MHz HFRCO, CPU running while loop from flash	—	120	TBD	μA/MHz
		72 MHz HFRCO, CPU running CoreMark loop from flash	—	140	—	μA/MHz
		50 MHz crystal, CPU running while loop from flash	—	123	—	μA/MHz
		48 MHz HFRCO, CPU running while loop from flash	—	122	TBD	μA/MHz
		32 MHz HFRCO, CPU running while loop from flash	—	124	—	μA/MHz
		26 MHz HFRCO, CPU running while loop from flash	—	126	TBD	μA/MHz
		16 MHz HFRCO, CPU running while loop from flash	—	131	—	μA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	319	TBD	μA/MHz
Current consumption in EM0 mode with all peripherals disabled and voltage scaling enabled	I <sub>ACTIVE_VS</sub>	19 MHz HFRCO, CPU running while loop from flash	—	107	—	μA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	262	—	μA/MHz
Current consumption in EM1 mode with all peripherals disabled	I <sub>EM1</sub>	72 MHz HFRCO	—	57	TBD	μA/MHz
		50 MHz crystal	—	60	—	μA/MHz
		48 MHz HFRCO	—	59	TBD	μA/MHz
		32 MHz HFRCO	—	61	—	μA/MHz
		26 MHz HFRCO	—	63	TBD	μA/MHz
		16 MHz HFRCO	—	68	—	μA/MHz
		1 MHz HFRCO	—	255	TBD	μA/MHz
Current consumption in EM1 mode with all peripherals disabled and voltage scaling enabled	I <sub>EM1_VS</sub>	19 MHz HFRCO	—	55	—	μA/MHz
		1 MHz HFRCO	—	210	—	μA/MHz

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM2 mode, with voltage scaling enabled	I <sub>EM2_VS</sub>	Full 512 kB RAM retention and RTCC running from LFXO	—	3.9	—	μA
		Full 512 kB RAM retention and RTCC running from LFRCO	—	4.3	—	μA
		16 kB (1 bank) RAM retention and RTCC running from LFRCO <sup>2</sup>	—	2.8	TBD	μA
Current consumption in EM3 mode, with voltage scaling enabled	I <sub>EM3_VS</sub>	Full 512 kB RAM retention and CRYOTIMER running from ULFRCO	—	3.6	TBD	μA
Current consumption in EM4H mode, with voltage scaling enabled	I <sub>EM4H_VS</sub>	128 byte RAM retention, RTCC running from LFXO	—	1.08	—	μA
		128 byte RAM retention, CRYOTIMER running from ULFRCO	—	0.69	—	μA
		128 byte RAM retention, no RTCC	—	0.69	TBD	μA
Current consumption in EM4S mode	I <sub>EM4S</sub>	No RAM retention, no RTCC	—	0.16	TBD	μA
Current consumption of peripheral power domain 1, with voltage scaling enabled	I <sub>PD1_VS</sub>	Additional current consumption in EM2/3 when any peripherals on power domain 1 are enabled <sup>1</sup>	—	0.68	—	μA
Current consumption of peripheral power domain 2, with voltage scaling enabled	I <sub>PD2_VS</sub>	Additional current consumption in EM2/3 when any peripherals on power domain 2 are enabled <sup>1</sup>	—	0.28	—	μA

**Note:**

1. Extra current consumed by power domain. Does not include current associated with the enabled peripherals. See [3.2.4 EM2 and EM3 Power Domains](#) for a list of the peripherals in each power domain.
2. CMU\_LFRCTRL\_ENVREF = 1, CMU\_LFRCTRL\_VREFUPDATE = 1

#### 4.1.7.2 Current Consumption 3.3 V using DC-DC Converter

Unless otherwise indicated, typical conditions are: VREGVDD = AVDD = IOVDD = 3.3 V, DVDD = 1.8 V DC-DC output. T = 25 °C. Minimum and maximum values in this table represent the worst conditions across supply voltage and process variation at T = 25 °C.

**Table 4.8. Current Consumption 3.3 V using DC-DC Converter**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM0 mode with all peripherals disabled, DCDC in Low Noise DCM mode <sup>2</sup>	I <sub>ACTIVE_DCM</sub>	72 MHz HFRCO, CPU running Prime from flash	—	80	—	μA/MHz
		72 MHz HFRCO, CPU running while loop from flash	—	80	—	μA/MHz
		72 MHz HFRCO, CPU running CoreMark loop from flash	—	92	—	μA/MHz
		50 MHz crystal, CPU running while loop from flash	—	84	—	μA/MHz
		48 MHz HFRCO, CPU running while loop from flash	—	84	—	μA/MHz
		32 MHz HFRCO, CPU running while loop from flash	—	90	—	μA/MHz
		26 MHz HFRCO, CPU running while loop from flash	—	94	—	μA/MHz
		16 MHz HFRCO, CPU running while loop from flash	—	109	—	μA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	698	—	μA/MHz
Current consumption in EM0 mode with all peripherals disabled, DCDC in Low Noise CCM mode <sup>1</sup>	I <sub>ACTIVE_CCM</sub>	72 MHz HFRCO, CPU running Prime from flash	—	84	—	μA/MHz
		72 MHz HFRCO, CPU running while loop from flash	—	84	—	μA/MHz
		72 MHz HFRCO, CPU running CoreMark loop from flash	—	95	—	μA/MHz
		50 MHz crystal, CPU running while loop from flash	—	91	—	μA/MHz
		48 MHz HFRCO, CPU running while loop from flash	—	92	—	μA/MHz
		32 MHz HFRCO, CPU running while loop from flash	—	104	—	μA/MHz
		26 MHz HFRCO, CPU running while loop from flash	—	113	—	μA/MHz
		16 MHz HFRCO, CPU running while loop from flash	—	142	—	μA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	1264	—	μA/MHz

#### 4.1.10.2 High-Frequency Crystal Oscillator (HFXO)

Table 4.13. High-Frequency Crystal Oscillator (HFXO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal frequency	$f_{\text{HFXO}}$	No clock doubling	4	—	50	MHz
		Clock doubler enabled	TBD	—	TBD	MHz
Supported crystal equivalent series resistance (ESR)	$\text{ESR}_{\text{HFXO}}$	50 MHz crystal	—	—	50	$\Omega$
		24 MHz crystal	—	—	150	$\Omega$
		4 MHz crystal	—	—	180	$\Omega$
Nominal on-chip tuning cap range <sup>1</sup>	$C_{\text{HFXO\_T}}$	On each of HFXTAL_N and HFXTAL_P pins	8.7	—	51.7	pF
On-chip tuning capacitance step	$\text{SS}_{\text{HFXO}}$		—	0.084	—	pF
Startup time	$t_{\text{HFXO}}$	50 MHz crystal, ESR = 50 Ohm, $C_L = 8$ pF	—	350	—	$\mu\text{s}$
		24 MHz crystal, ESR = 150 Ohm, $C_L = 6$ pF	—	700	—	$\mu\text{s}$
		4 MHz crystal, ESR = 180 Ohm, $C_L = 18$ pF	—	3	—	ms
Current consumption after startup	$I_{\text{HFXO}}$	50 MHz crystal	—	880	—	$\mu\text{A}$
		24 MHz crystal	—	420	—	$\mu\text{A}$
		4 MHz crystal	—	80	—	$\mu\text{A}$

**Note:**

1. The effective load capacitance seen by the crystal will be  $C_{\text{HFXO\_T}}/2$ . This is because each XTAL pin has a tuning cap and the two caps will be seen in series by the crystal.



#### 4.1.12 General-Purpose I/O (GPIO)

Table 4.20. General-Purpose I/O (GPIO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input low voltage	$V_{IL}$	GPIO pins	—	—	$IOVDD \cdot 0.3$	V
Input high voltage	$V_{IH}$	GPIO pins	$IOVDD \cdot 0.7$	—	—	V
Output high voltage relative to IOVDD	$V_{OH}$	Sourcing 3 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	$IOVDD \cdot 0.8$	—	—	V
		Sourcing 1.2 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	$IOVDD \cdot 0.6$	—	—	V
		Sourcing 20 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	$IOVDD \cdot 0.8$	—	—	V
		Sourcing 8 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	$IOVDD \cdot 0.6$	—	—	V
Output low voltage relative to IOVDD	$V_{OL}$	Sinking 3 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	—	—	$IOVDD \cdot 0.2$	V
		Sinking 1.2 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	—	—	$IOVDD \cdot 0.4$	V
		Sinking 20 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	—	—	$IOVDD \cdot 0.2$	V
		Sinking 8 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	—	—	$IOVDD \cdot 0.4$	V
Input leakage current	$I_{IOLEAK}$	All GPIO except LFXO pins, GPIO $\leq IOVDD$ , $T \leq 85$ °C	—	0.1	TBD	nA
		LFXO Pins, GPIO $\leq IOVDD$ , $T \leq 85$ °C	—	0.1	TBD	nA
		All GPIO except LFXO pins, GPIO $\leq IOVDD$ , $T > 85$ °C	—	—	TBD	nA
		LFXO Pins, GPIO $\leq IOVDD$ , $T > 85$ °C	—	—	TBD	nA
Input leakage current on 5VTOL pads above IOVDD	$I_{5VTOLLEAK}$	$IOVDD < GPIO \leq IOVDD + 2$ V	—	3.3	TBD	μA
I/O pin pull-up/pull-down resistor	$R_{PUD}$		TBD	40	TBD	kΩ
Pulse width of pulses removed by the glitch suppression filter	$t_{IOGLITCH}$		15	25	35	ns

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Signal to noise and distortion ratio (1 kHz sine wave), Noise band limited to 250 kHz	SNDR <sub>DAC</sub>	500 ksps, single-ended, internal 1.25V reference	—	60.4	—	dB
		500 ksps, single-ended, internal 2.5V reference	—	61.6	—	dB
		500 ksps, single-ended, 3.3V VDD reference	—	64.0	—	dB
		500 ksps, differential, internal 1.25V reference	—	63.3	—	dB
		500 ksps, differential, internal 2.5V reference	—	64.4	—	dB
		500 ksps, differential, 3.3V VDD reference	—	65.8	—	dB
Signal to noise and distortion ratio (1 kHz sine wave), Noise band limited to 22 kHz	SNDR <sub>DAC_BAND</sub>	500 ksps, single-ended, internal 1.25V reference	—	65.3	—	dB
		500 ksps, single-ended, internal 2.5V reference	—	66.7	—	dB
		500 ksps, differential, 3.3V VDD reference	—	68.5	—	dB
		500 ksps, differential, internal 1.25V reference	—	67.8	—	dB
		500 ksps, differential, internal 2.5V reference	—	69.0	—	dB
		500 ksps, single-ended, 3.3V VDD reference	—	70.0	—	dB
Total harmonic distortion	THD		—	70.2	—	dB
Differential non-linearity <sup>3</sup>	DNL <sub>DAC</sub>		TBD	—	TBD	LSB
Integral non-linearity	INL <sub>DAC</sub>		TBD	—	TBD	LSB
Offset error <sup>5</sup>	V <sub>OFFSET</sub>	T = 25 °C	TBD	—	TBD	mV
		Across operating temperature range	TBD	—	TBD	mV
Gain error <sup>5</sup>	V <sub>GAIN</sub>	T = 25 °C, Low-noise internal reference (REFSEL = 1V25LN or 2V5LN)	TBD	—	TBD	%
		Across operating temperature range, Low-noise internal reference (REFSEL = 1V25LN or 2V5LN)	TBD	—	TBD	%
External load capacitance, OUTSCALE=0	C <sub>LOAD</sub>		—	—	75	pF

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Note:</b> <ol style="list-style-type: none"> <li>Specified configuration for 3X-Gain configuration is: INCBW = 1, HCMDIS = 1, RESINSEL = VSS, <math>V_{\text{INPUT}} = 0.5 \text{ V}</math>, <math>V_{\text{OUTPUT}} = 1.5 \text{ V}</math>. Nominal voltage gain is 3.</li> <li>If the maximum <math>C_{\text{LOAD}}</math> is exceeded, an isolation resistor is required for stability. See AN0038 for more information.</li> <li>When INCBW is set to 1 the OPAMP bandwidth is increased. This is allowed only when the non-inverting close-loop gain is <math>\geq 3</math>, or the OPAMP may not be stable.</li> <li>Current into the load resistor is excluded. When the OPAMP is connected with closed-loop gain <math>&gt; 1</math>, there will be extra current to drive the resistor feedback network. The internal resistor feedback network has total resistance of 143.5 kOhm, which will cause another <math>\sim 10 \mu\text{A}</math> current when the OPAMP drives 1.5 V between output and ground.</li> <li>Step between 0.2V and <math>V_{\text{OPA}} - 0.2\text{V}</math>, 10%-90% rising/falling range.</li> <li>From enable to output settled. In sample-and-off mode, RC network after OPAMP will contribute extra delay. Settling error <math>&lt; 1\text{mV}</math>.</li> <li>In unit gain connection, UGF is the gain-bandwidth product of the OPAMP. In 3x Gain connection, UGF is the gain-bandwidth product of the OPAMP and 1/3 attenuation of the feedback network.</li> <li>Specified configuration for Unit gain buffer configuration is: INCBW = 0, HCMDIS = 0, RESINSEL = DISABLE. <math>V_{\text{INPUT}} = 0.5 \text{ V}</math>, <math>V_{\text{OUTPUT}} = 0.5 \text{ V}</math>.</li> <li>When HCMDIS=1 and input common mode transitions the region from <math>V_{\text{OPA}} - 1.4\text{V}</math> to <math>V_{\text{OPA}} - 1\text{V}</math>, input offset will change. PSRR and CMRR specifications do not apply to this transition region.</li> </ol>						

#### 4.1.20 LCD Driver

Table 4.28. LCD Driver

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Frame rate	$f_{\text{LCDFR}}$		TBD	—	TBD	Hz
LCD supply range <sup>2</sup>	$V_{\text{LCDIN}}$		1.8	—	3.8	V
LCD output voltage range	$V_{\text{LCD}}$	Current source mode, No external LCD capacitor	2.0	—	$V_{\text{LCDIN}} - 0.4$	V
		Step-down mode with external LCD capacitor	2.0	—	$V_{\text{LCDIN}}$	V
		Charge pump mode with external LCD capacitor	2.0	—	1.9 * $V_{\text{LCDIN}}$	V
Contrast control step size	$\text{STEP}_{\text{CONTRAST}}$	Current source mode	—	64	—	mV
		Charge pump or Step-down mode	—	43	—	mV
Contrast control step accuracy <sup>1</sup>	$\text{ACC}_{\text{CONTRAST}}$		—	+/-4	—	%
<b>Note:</b> <ol style="list-style-type: none"> <li>Step size accuracy is measured relative to the typical step size, and typ value represents one standard deviation.</li> <li><math>V_{\text{LCDIN}}</math> is selectable between the AVDD or DVDD supply pins, depending on EMU_PWRCTRL_ANASW.</li> </ol>						

### 4.1.23.3 I2C Fast-mode Plus (Fm+)<sup>1</sup>

**Table 4.33. I2C Fast-mode Plus (Fm+)<sup>1</sup>**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SCL clock frequency <sup>2</sup>	f <sub>SCL</sub>		0	—	1000	kHz
SCL clock low time	t <sub>LOW</sub>		0.5	—	—	μs
SCL clock high time	t <sub>HIGH</sub>		0.26	—	—	μs
SDA set-up time	t <sub>SU_DAT</sub>		50	—	—	ns
SDA hold time	t <sub>HD_DAT</sub>		100	—	—	ns
Repeated START condition set-up time	t <sub>SU_STA</sub>		0.26	—	—	μs
(Repeated) START condition hold time	t <sub>HD_STA</sub>		0.26	—	—	μs
STOP condition set-up time	t <sub>SU_STO</sub>		0.26	—	—	μs
Bus free time between a STOP and START condition	t <sub>BUF</sub>		0.5	—	—	μs

**Note:**

1. For CLHR set to 0 or 1 in the I2Cn\_CTRL register.
2. For the minimum HPERCLK frequency required in Fast-mode Plus, refer to the I2C chapter in the reference manual.

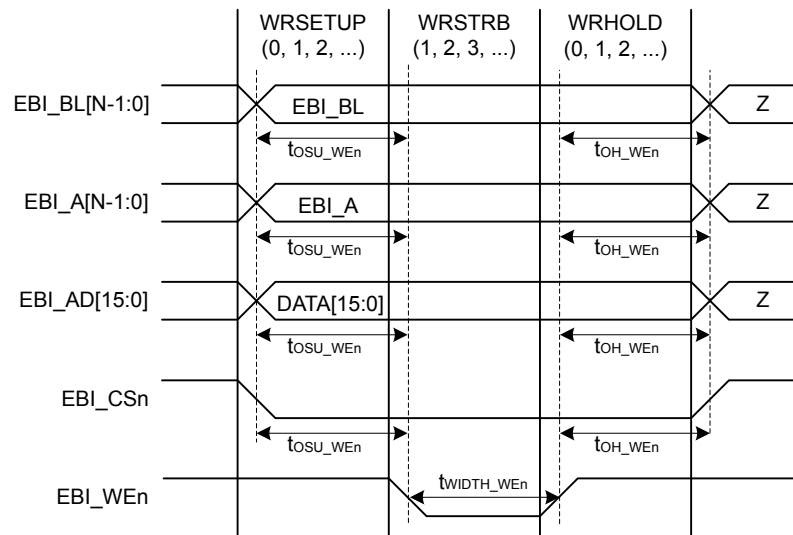
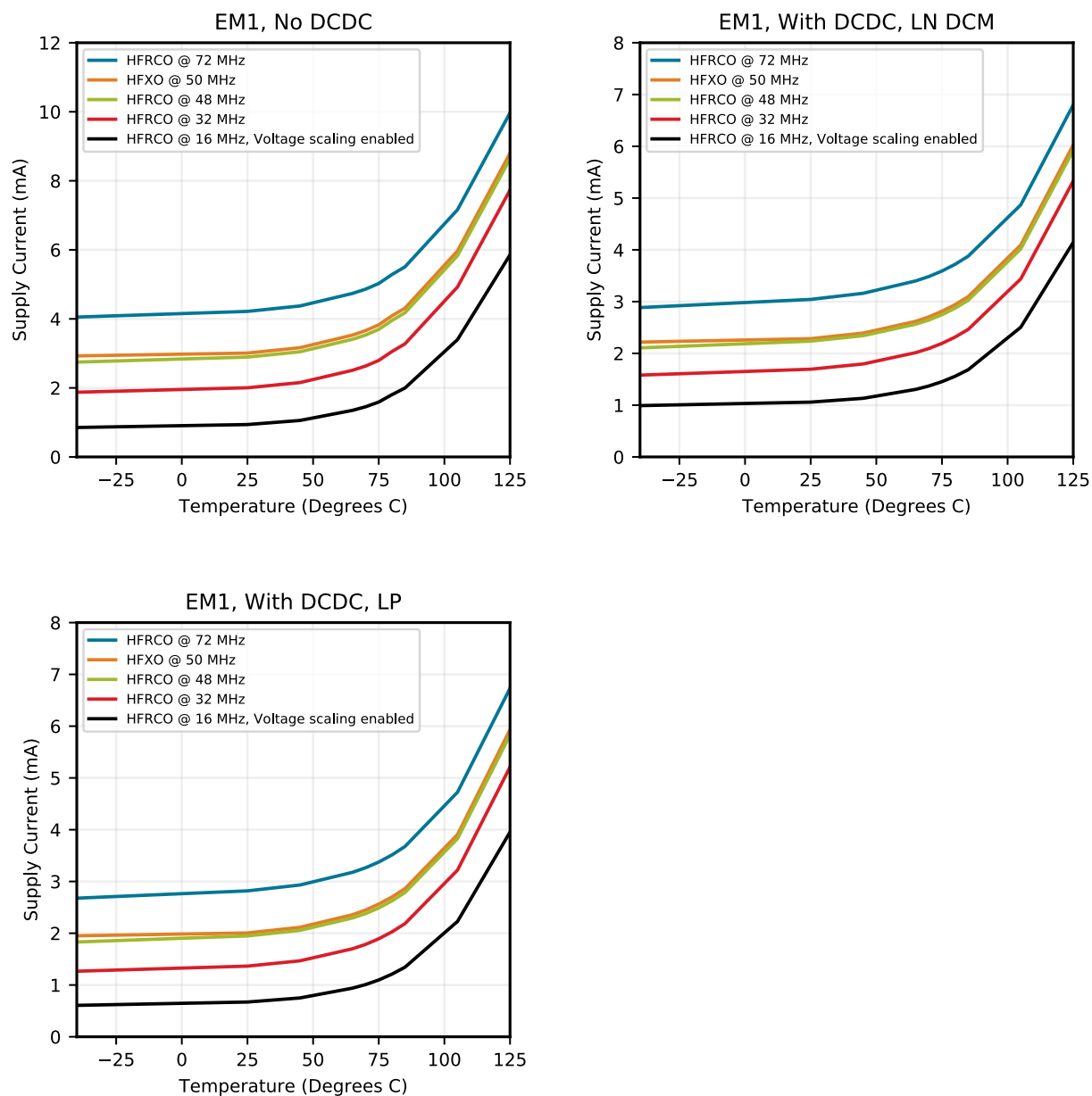


Figure 4.3. EBI Write Enable Output Timing Diagram

## 4.2 Typical Performance Curves

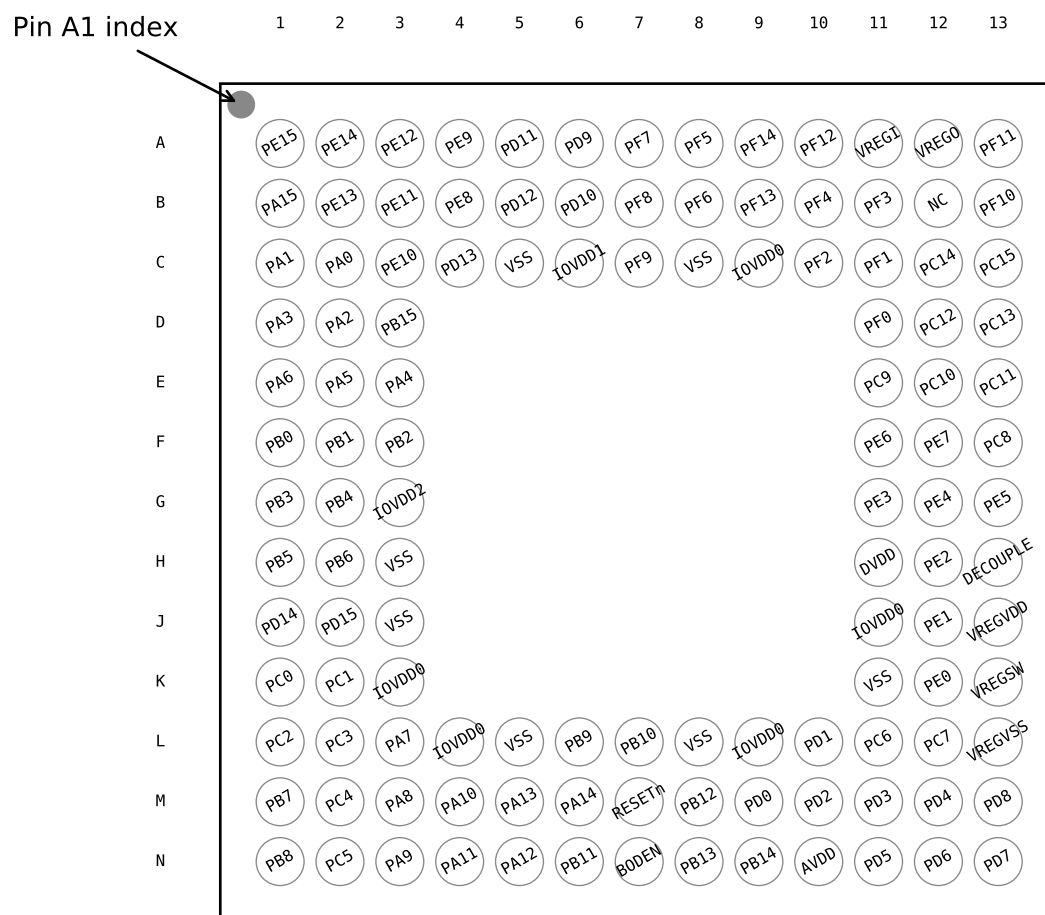
Typical performance curves indicate typical characterized performance under the stated conditions.



**Figure 4.25. EM1 Sleep Mode Typical Supply Current vs. Temperature**

Typical supply current for EM2, EM3 and EM4H using standard software libraries from Silicon Laboratories.

## 5.4 EFM32GG11B5xx in BGA120 Device Pinout



**Figure 5.4. EFM32GG11B5xx in BGA120 Device Pinout**

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see [5.20 GPIO Functionality Table](#) or [5.21 Alternate Functionality Overview](#).

**Table 5.4. EFM32GG11B5xx in BGA120 Device Pinout**

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE15	A1	GPIO	PE14	A2	GPIO
PE12	A3	GPIO	PE9	A4	GPIO
PD11	A5	GPIO	PD9	A6	GPIO
PF7	A7	GPIO	PF5	A8	GPIO
PF14	A9	GPIO (5V)	PF12	A10	GPIO
VREGI	A11	Input to 5 V regulator.	VREGO	A12	Decoupling for 5 V regulator and regulator output. Power for USB PHY in USB-enabled OPNs



## 5.7 EFM32GG11B3xx in BGA112 Device Pinout

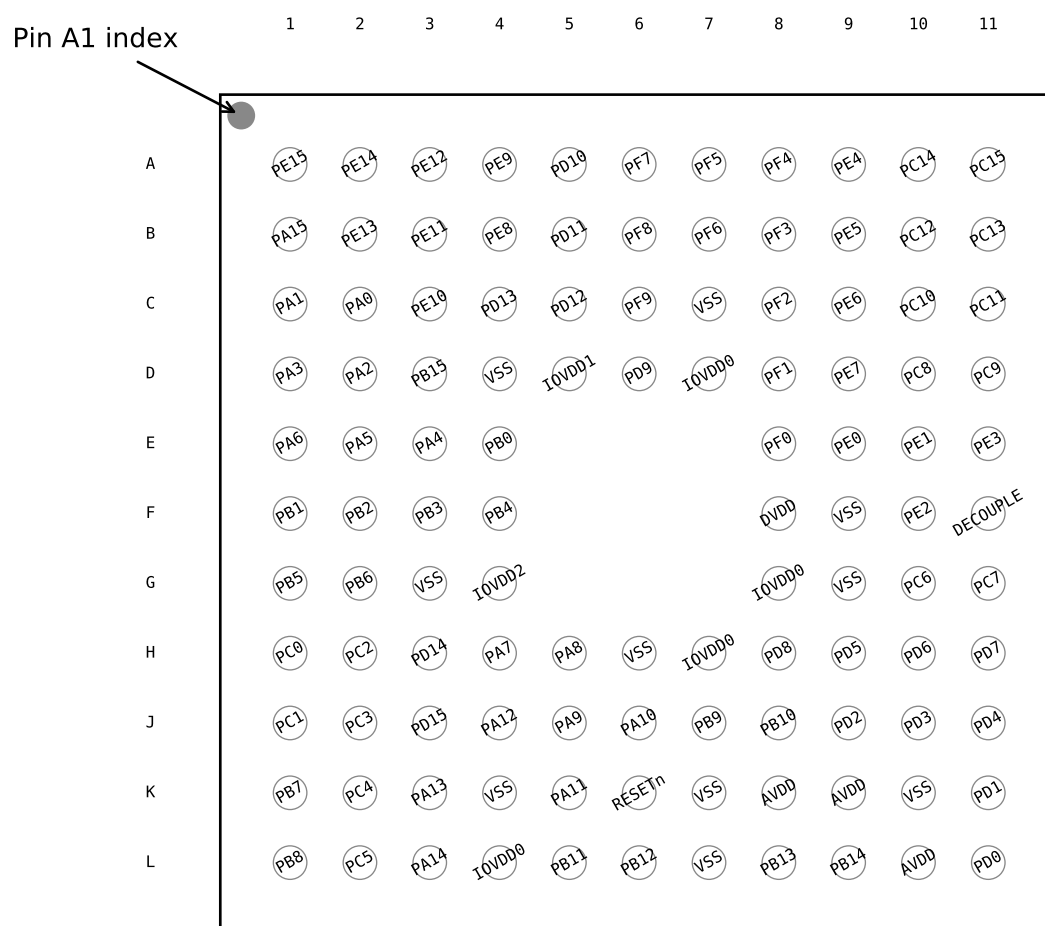


Figure 5.7. EFM32GG11B3xx in BGA112 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see [5.20 GPIO Functionality Table](#) or [5.21 Alternate Functionality Overview](#).

Table 5.7. EFM32GG11B3xx in BGA112 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE15	A1	GPIO	PE14	A2	GPIO
PE12	A3	GPIO	PE9	A4	GPIO
PD10	A5	GPIO	PF7	A6	GPIO
PF5	A7	GPIO	PF4	A8	GPIO
PE4	A9	GPIO	PC14	A10	GPIO (5V)
PC15	A11	GPIO (5V)	PA15	B1	GPIO
PE13	B2	GPIO	PE11	B3	GPIO

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PC4	13	GPIO	PC5	14	GPIO
PB7	15	GPIO	PB8	16	GPIO
PA8	17	GPIO	PA9	18	GPIO
PA10	19	GPIO	RESETn	20	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.
PB11	21	GPIO	AVDD	23 27	Analog power supply.
PB13	24	GPIO	PB14	25	GPIO
PD0	28	GPIO (5V)	PD1	29	GPIO
PD2	30	GPIO (5V)	PD3	31	GPIO
PD4	32	GPIO	PD5	33	GPIO
PD6	34	GPIO	PD7	35	GPIO
PD8	36	GPIO	PC6	37	GPIO
PC7	38	GPIO	DVDD	39	Digital power supply.
DECOUPLE	40	Decouple output for on-chip voltage regulator. An external decoupling capacitor is required at this pin.	PC8	41	GPIO (5V)
PC9	42	GPIO (5V)	PC10	43	GPIO (5V)
PC11	44	GPIO (5V)	PC12	45	GPIO (5V)
PC13	46	GPIO (5V)	PC14	47	GPIO (5V)
PC15	48	GPIO (5V)	PF0	49	GPIO (5V)
PF1	50	GPIO (5V)	PF2	51	GPIO
PF3	52	GPIO	PF4	53	GPIO
PF5	54	GPIO	PE8	57	GPIO
PE9	58	GPIO	PE10	59	GPIO
PE11	60	GPIO	PE12	61	GPIO
PE13	62	GPIO	PE14	63	GPIO
PE15	64	GPIO			

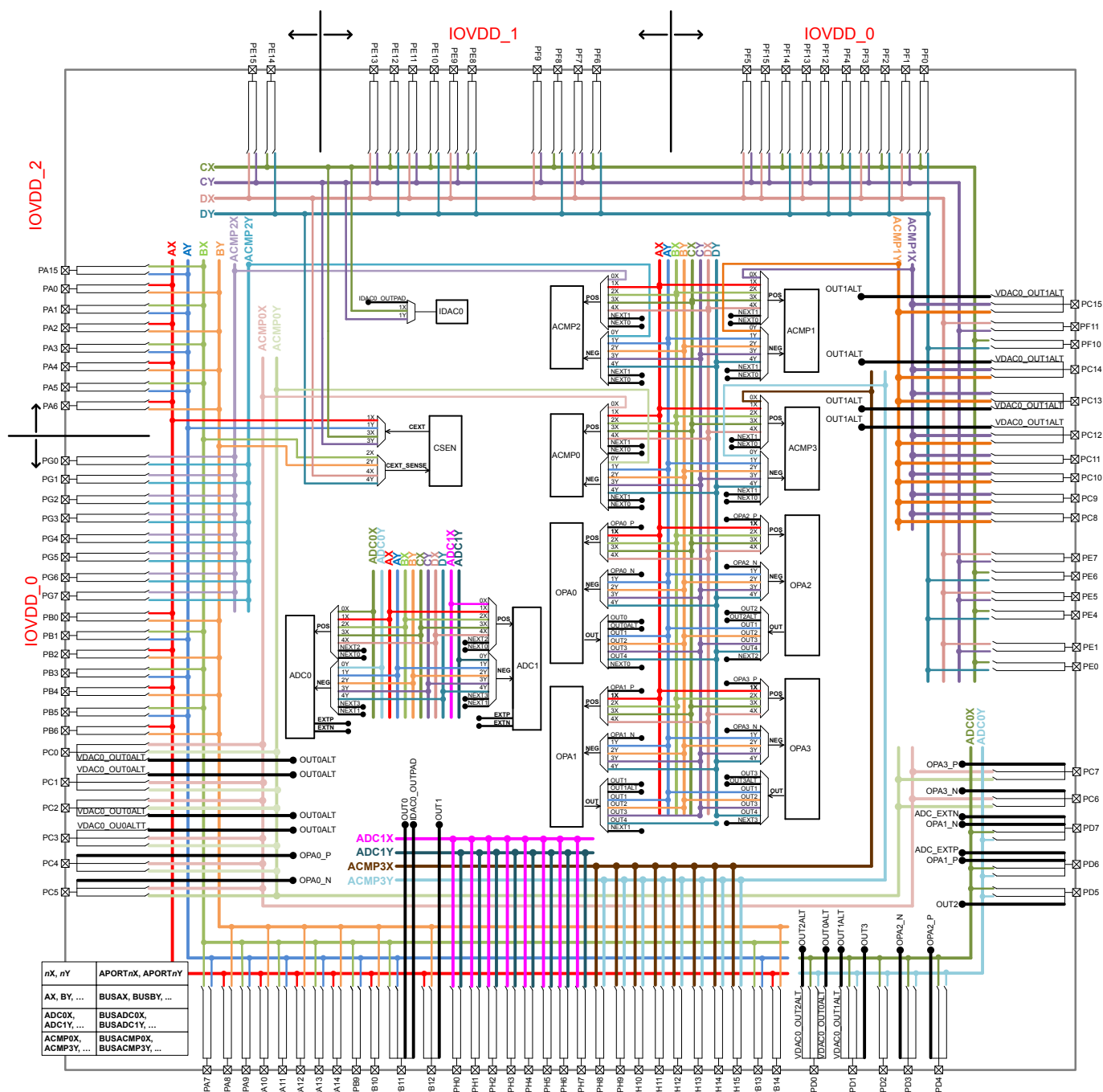
**Note:**

1. GPIO with 5V tolerance are indicated by (5V).

GPIO Name	Pin Alternate Functionality / Description				
	Analog	EBI	Timers	Communication	Other
PD13		EBI_ARDY #1	TIM2_CDTI0 #1 TIM3_CC1 #6 WTIM0_CC1 #1	ETH_MDIO #1 US4_CTS #1 US5_CLK #1	ETM_TD1 #1
PI15				CAN1_TX #7 US3_CS #5	
PI14				CAN1_RX #7 US3_CLK #5	
PI13				CAN0_TX #7 US3_RX #5	
PI12				CAN0_RX #7 US3_TX #5	
PI10		EBI_A15 #2	TIM4_CC2 #3	US4_CTS #3	
PI7		EBI_A12 #2	TIM1_CC1 #7 TIM4_CC2 #2 WTIM3_CC1 #5	US4_RX #3	
PF15	BUSCY BUSDX		TIM1_CC2 #6 TIM4_CC2 #1 WTIM3_CC2 #7	US5_TX #2 I2C2_SDA #5	
PF12	BUSDY BUSCX	EBI_NANDREn #5	TIM4_CC2 #0 TIM1_CC3 #5 TIM5_CC0 #7 WTIM3_CC2 #6	US5_CS #2 I2C2_SCL #3 USB_ID	
PF4	BUSDY BUSCX LCD_SEG2	EBI_WEn #0 EBI_WEn #5	TIM4_CC1 #0 TIM0_CDTI1 #2 TIM1_CC2 #5 WTIM3_CC1 #6	US1_RTS #2 I2C2_SDA #3	PRS_CH1 #1
PC15	VDAC0_OUT1ALT / OPA1_OUTALT #3 BUSACMP1Y BU- SACMP1X	EBI_NANDREn #4	TIM0_CDTI2 #1 TIM1_CC2 #0 WTIM0_CC0 #4 LE- TIM0_OUT1 #5	US0_CLK #3 US1_CLK #3 US3_RTS #3 U0_RX #3 U1_RTS #0 LEU0_RX #5 I2C2_SCL #1	LES_CH15 PRS_CH1 #2 ACMP3_O #1 DBG_SWO #1
PC14	VDAC0_OUT1ALT / OPA1_OUTALT #2 BUSACMP1Y BU- SACMP1X	EBI_NANDWEn #4	TIM0_CDTI1 #1 TIM1_CC1 #0 TIM1_CC3 #4 TIM5_CC0 #6 WTIM3_CC0 #3 LE- TIM0_OUT0 #5 PCNT0_S1IN #0	US0_CS #3 US1_CS #3 US2_RTS #3 US3_CS #2 U0_TX #3 U1_CTS #0 LEU0_TX #5 I2C2_SDA #1	LES_CH14 PRS_CH0 #2 ACMP3_O #2
PA2	BUSBY BUSAX LCD_SEG15	EBI_AD11 #0 EBI_DTEN #3	TIM0_CC2 #0 TIM3_CC2 #4	ETH_RMIIRXD0 #0 ETH_MIITXD2 #0 SDIO_DAT2 #1 US1_RX #6 US3_CLK #0 QSPIO_DQ0 #1	CMU_CLK0 #0 PRS_CH8 #1 ETM_TD0 #3
PG0	BUSACMP2Y BU- SACMP2X	EBI_AD00 #2	TIM6_CC0 #0 TIM2_CDTI0 #3 WTIM0_CDTI1 #1 LETIM1_OUT0 #6	ETH_MIITXCLK #1 US3_TX #4 QSPIO_SCLK #2	CMU_CLK2 #3

## 5.22 Analog Port (APORT) Client Maps

The Analog Port (APORT) is an infrastructure used to connect chip pins with on-chip analog clients such as analog comparators, ADCs, DACs, etc. The APORT consists of a set of shared buses, switches, and control logic needed to configurably implement the signal routing. [Figure 5.20 APORT Connection Diagram on page 211](#) shows the APORT routing for this device family (note that available features may vary by part number). A complete description of APORT functionality can be found in the Reference Manual.



### Table 5.31. VDACC0 / OPA Bus and Pin Mapping

[illegible]